Amdt. dated January 29, 2009 Reply to Office Action dated October 30, 2008

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) An in-plane switching mode liquid crystal display device, comprising:

a plurality of gate lines and data lines defining a plurality of pixels;

a thin film transistor in each of the pixels, the thin film transistor including a gate electrode on a substrate, an insulating layer over the gate electrode, a semiconductor layer on the insulating layer, a source electrode and a drain electrode on the semiconductor layer;

a common line on the substrate;

at least one pixel electrode having a predetermined width in each of the pixels; and at least one common electrode having a predetermined width completely overlapping a data line in width, the common electrode being substantially parallel to the pixel electrode and the common electrode being alternately disposed with the pixel electrode;

a passivation layer over the source electrode, drain electrode and semiconductor layer, the passivation layer being made of an organic material including <u>at least one material of BCB</u> (Benzo-Cyclo-Butene) and photoacryl; and

wherein the pixel electrode and the common electrode are disposed on the same layer, the common electrode and the common line are disposed on layers different from each other so that the common electrode is connected to the common line through a contact hole, the pixel electrode and the common electrode being disposed on the passivation layer,

wherein the common electrode and the common line are not overlapped with the pixel electrode and the common line is separated a predetermined distance from the end portion of the pixel electrode.

2-3. (Cancelled)

4. (Previously Presented) The device of claim 1, wherein the data lines are formed on the insulating layer.

5-9. (Cancelled)

10. (Currently Amended) An in-plane switching mode liquid crystal display device,

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comprising:

a plurality of gate lines and data lines defining a plurality of pixels;

a thin film transistor in each pixel, the thin film transistor including a gate electrode on a substrate, an insulating layer over the gate electrode, a semiconductor layer on the insulating layer, a source electrode and a drain electrode on the semiconductor layer, and a passivation layer over the source electrode, drain electrode and semiconductor layer, the passivation layer being made of at least one material of BCB (Benzo-Cyclo-Butene) and photoacryl;

a common line on the substrate;

at least one pixel electrode in each pixel;

a first common electrode completely overlapping a data line in width; and

at least one second common electrode in each pixel, the second common electrode connected to the common lines,

wherein the pixel electrode has a predetermined width and is substantially parallel to the first and second common electrodes and the pixel electrode and the common electrode are disposed on the same layer, the <u>source pixel</u> electrode is disposed between the first and second common electrodes and between the <u>first second</u> common electrodes, the <u>pixel electrode and the</u> common electrode being disposed on the passivation layer,

wherein the common electrode and the common line are not overlapped with the pixel electrode and the common line is separated a predetermined distance from the end portion of the pixel electrode.

11. (Original) The device of claim 10, wherein a width of the first common electrode is larger than that of the second common electrode.

12-16. (Cancelled)